

Inchange Semiconductor

Product Specification

Silicon NPN Darlington Power Transistors

2SD1895

DESCRIPTION

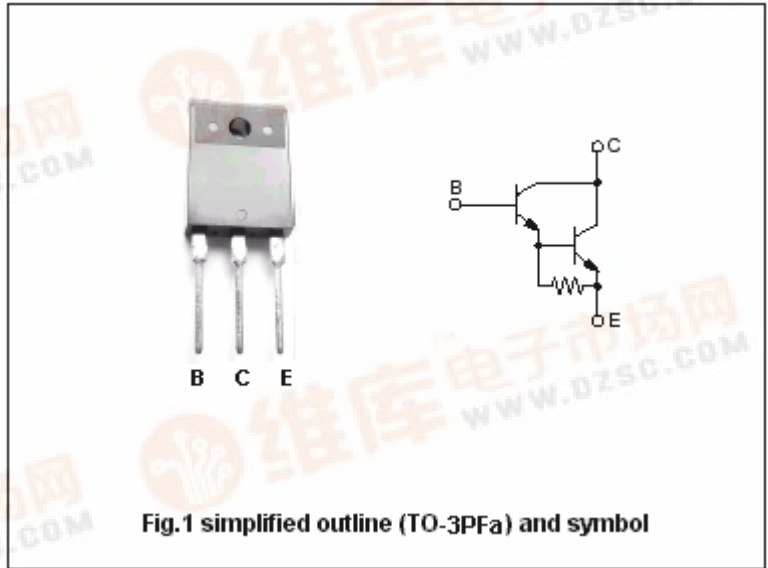
- With TO-3PFa package
- High DC current gain
- Low collector saturation voltage
- Complement to type 2SB1255

APPLICATIONS

- Power amplification
- Optimum for 90W high-fidelity output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	140	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _{CP}	Collector current-peak		8	A
P _C	Collector power dissipation	T _C =25	100	W
			3	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA ; I _B =0	140			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =7A ; I _B =7mA			2.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =7A ; I _B =7mA			3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =160V; I _E =0			100	μ A
I _{CEO}	Collector cut-off current	V _{CE} =140V; I _B =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	2000			
h _{FE-2}	DC current gain	I _C =7A ; V _{CE} =5V	5000		30000	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V; f=1MHz		20		MHz

Switching times

t _{on}	Turn-on time	I _C =7A; V _{CC} =50V I _{B1} =-I _{B2} =7mA		2.0		μ s
t _{stg}	Storage time			6.0		μ s
t _f	Fall time			1.2		μ s

◆ h_{FE-2} classifications

Q	P
5000-15000	8000-30000

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PACKAGE OUTLINE

